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In the Specification:

At page 1, please amend the paragraph starting on line 7 as follows:

This application is a division of U.S. Application Serial No. 08/932,025, entitled 'Method And Apparatus For Low Energy Electron Enhanced Etching of Substrates in an AC or DC Plasma Environment, filed September 17, 1997 now U.S. Pat. No. 6,258,287, which claims priority to and the benefit of the filing date of Provisional Patent Application Serial Nos. 60/026,985, filed September 20, 1996, entitled "APPARATUS AND PROCESS FOR LOW-DAMAGE DRY ETCHING OF INSULATORS BY LOW ENERGY ELECTRON ENHANCED ETCHING IN A DC PLASMA"; 60/026,587, filed September 20, 1996, entitled "APPARATUS AND PROCESS FOR LOW-DAMAGE DRY ETCHING OF INSULATORS BY LOW ENERGY ELECTRON ENHANCED ETCHING IN AN AC PLASMA"; and is a Continuation-In-Part of U.S. Patent Application Serial No. 08/705,902, filed on August 28, 1996 now U.S. Pat. No. 5,882,538 entitled "METHOD AND APPARATUS FOR LOW ENERGY ELECTRON ENHANCED ETCHING OF SUBSTRATES".

At page 1, please insert the following section title and paragraph immediately before the section titled "FIELD OF THE INVENTION":

**STATEMENT REGARDING FEDERALLY SPONSORED
RESEARCH OR DEVELOPMENT**

The U.S. government may have a paid-up license in this invention and the right in limited circumstances to require the patent owner to license others on reasonable terms as provided for by the terms of grant no. DMR-9202879 awarded by the National Science Foundation of the U.S.